	1 A A A A A A A A A A A A A A A A A A A
ΡΛΝ	JIT
	SEMI
	CONDUCTOR

20V P-Channel Enhancement Mode MOSFET

Current -7.2A

Features

Voltage

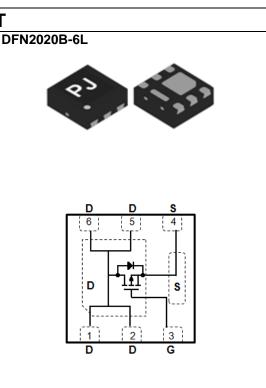
• R_{DS(ON)}, V_{GS}@-4.5V, I_D@-7.2A<32mΩ

-20 V

- $R_{DS(ON)}$, V_{GS} @-2.5V, I_D @-5.0A<39m Ω
- $R_{DS(ON)}$, $V_{GS}@-1.8V$, $I_D@-2.5A<48m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN2020B-6L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0003 ounces, 0.0086 grams



Maximum Ratings and Thermal Characteristics (T_A=25^oC unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Voltage	V _{GS}	<u>+</u> 8			
Continuous Drain Current (Note 4	ent (Note 4)		-7.2	A	
Pulsed Drain Current (Note 1)		I _{DM}	-28.8		
Power Dissipation	Ta=25⁰C	PD	2.8	W	
	Derate above 25°C		22	mW/∘C	
Operating Junction and Storage Temperature Range		Tj,Tstg	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient, t<10s (Note 4,5)		Reja	44.6	°C/W	



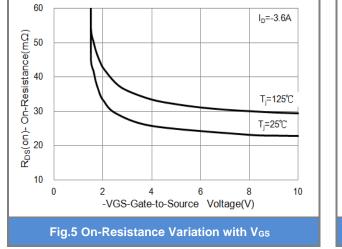
Electrical Characteristics (T_A=25°C unless otherwise noted)

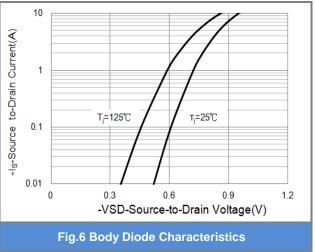
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static		-		_		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-20	-	- V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-0.35	-0.6	-0.9	v
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-7.2A	-	25	32	mΩ
		V _{GS} =-2.5V, I _D =-5A	-	30	39	
		Vgs=-1.8V, Id=-2.5A	-	35	48	
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-16V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	lgss	V _{GS} = <u>+</u> 8V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Qg		-	18.9	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =-10V, I _D =-7.2A,	-	2.8	-	
Gate-Drain Charge	Q_{gd}	V _{GS} =-4.5V ^(Note 2,3)	-	4.2	-	
Input Capacitance	Ciss	V _{DS} =-10V, V _{GS} =0V, f=1MHZ	-	1785	-	pF
Output Capacitance	Coss		-	152	-	
Reverse Transfer Capacitance	Crss		-	125	-	
Turn-On Delay Time	td _(on)		-	12	-	
Turn-On Rise Time	tr	V _{DS} =-10V, I _D =-7.2A, V _{GEN} =-4.5V, R _L =10Ω	-	68	-	
Turn-Off Delay Time	td _(off)		-	82	-	ns
Turn-Off Fall Time	tf	$R_G=6\Omega$ (Note 2,3)	-	35	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	ls		-	-	-1.5	А
Diode Forward Voltage	V _{SD}	Is=-1A, V _{GS} =0V	-	-0.64	-1.2	V

NOTES :

- 1. Pulse width <300us, Duty cycle <2%.
- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.
- 4. The maximum current rating is package limited.
- 5. R_{®JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

20 20 IÆ -4.5V -3V V_{DS}=-5V -I_{DS}-Drain-to-S ource Current(A) I_{DS}-Drain-to-Source Current(A) -2.5V 15 15 -2V 10 10 VGS=-1.5V 5 5 T_=125℃ T_**=25℃** 0 0 0 2 3 5 1 4 0.0 0.5 2.0 1.0 1.5 -VDS- Drain-to-Source Voltage(V) -VGS-Gate-to-Source Voltage(V) **Fig.1 On-Region Characteristics Fig.2 Transfer Characteristics** 50 1.4 R_{DS}(on)- On-Resistance (Normalized) $R_{DS}(on)$ - On-Resistance(m Ω) V_{GS}=-4.5V, I_D=-7.2A V_{GS}=-1.8V 1.3 40 V_{GS}=-2.5V, I_D=-5A 1.1 V_{GS}=-2.5V V_{GS}=-1.8V, I_D=-2.5A 30 1.0 V_{GS}=-4.5V 20 0.8 0 4 8 12 16 20 0 25 50 75 100 125 150 -IDS-Drain-to-Source Current(A) Temperature (℃) Fig.4 On-Resistance vs. Junction temperature Fig.3 On-Resistance vs. Drain Current 60 10





PANJ

SEMI

PJQ2405-AU

TYPICAL CHARACTERISTIC CURVES

2.5

175

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 $\begin{bmatrix} 5 \\ W_{DS}=-10V \\ I_{D}=-7.2A \end{bmatrix}$

TYPICAL CHARACTERISTIC CURVES

Fig.7 Gate-Charge Characteristics

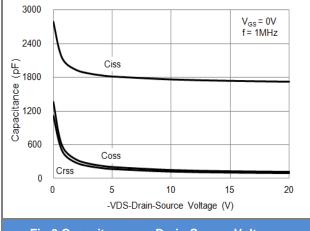


Fig.9 Capacitance vs. Drain-Source Voltage

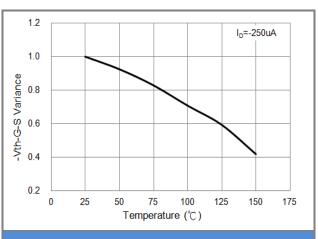


Fig.8 Threshold Voltage Variation with Temperature



PJQ2405-AU

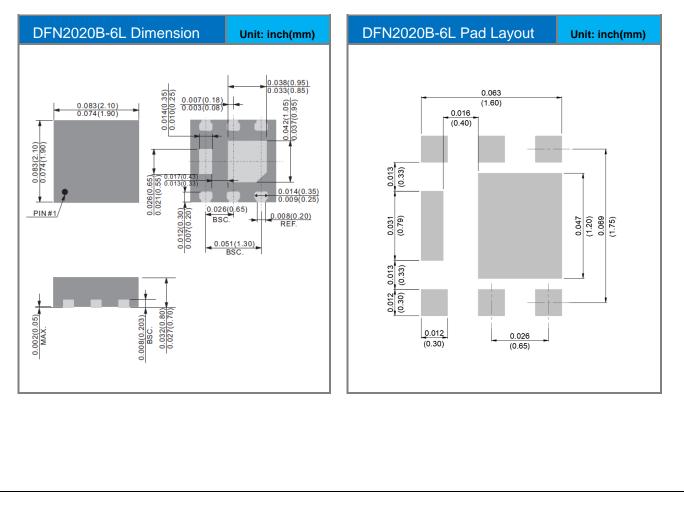
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Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ2405-AU_R1_000A1	DFN2020B-6L	3K pcs / 7" reel	405	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout





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